



BGU8063

low-noise high-linearity amplifier

Rev. 2 — 27 January 2017

Product data sheet

1 General description

The BGU8063 is, also known as the BTS3001H, a high-linearity bypass amplifier for wireless infrastructure applications, equipped with fast shutdown to support TDD systems. The LNA has a high input and output return loss and is designed to operate between 2.5 GHz and 4.0 GHz. It is housed in a 3 mm × 3 mm × 0.85 mm 10-terminal plastic thin small outline package. The LNA is ESD protected on all terminals.

2 Features and benefits

- Low-noise performance: NF = 1.4 dB
- High-linearity performance: IP_{3O} = 34 dBm
- High-input return loss > 10 dB
- High-output return loss > 10 dB
- Unconditionally stable up to 20 GHz
- Small 10-terminal leadless package 3 mm × 3 mm × 0.85 mm
- ESD protection on all terminals
- Moisture sensitivity level 1
- Fast shut down to support TDD systems
- +5 V single supply

3 Applications

- Wireless infrastructure
- Low-noise and high-linearity applications
- LTE, W-CDMA, CDMA, GSM
- General-purpose wireless applications
- TDD or FDD systems
- Suitable for small cells



4 Quick reference data

Table 1. Quick reference data

$f = 2500\text{ MHz}$; $V_{CC} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; input and output $50\text{ }\Omega$; unless otherwise specified. All RF parameters are measured on an application board with the circuit as shown in Figure 29 and components listed in Table 9 implemented. This board is optimized for $f = 2500\text{ MHz}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CC}	supply current	LNA enable; bypass off	-	75	90	mA
		LNA disable; bypass on	-	3	5	mA
G _{ass}	associated gain	LNA enable; bypass off	17.0	18.5	20	dB
		LNA disable; bypass on	-2.2	-1.8	-	dB
NF	noise figure	LNA enable; bypass off ^[1]	-	1.4	2.2	dB
P _{L(1dB)}	output power at 1 dB gain compression	LNA enable; bypass off	17.5	19.0	-	dBm
IP _{3O}	output third-order intercept point	2-tone; tone spacing = 1 MHz; P _L = 5 dBm per tone				
		LNA enable; bypass off	31.0	34.0	-	dBm
		LNA disable; bypass on	-	43.0	-	dBm

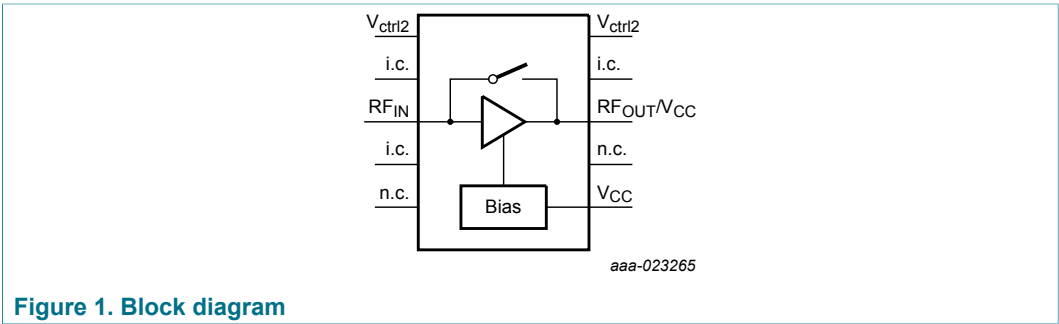
[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

5 Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BGU8063	HVSON10	plastic thermal enhanced very thin small outline package; no leads; 10 terminals; body 3 mm × 3 mm × 0.85 mm	SOT650-2

6 Block diagram



7 Pinning information

7.1 Pinning

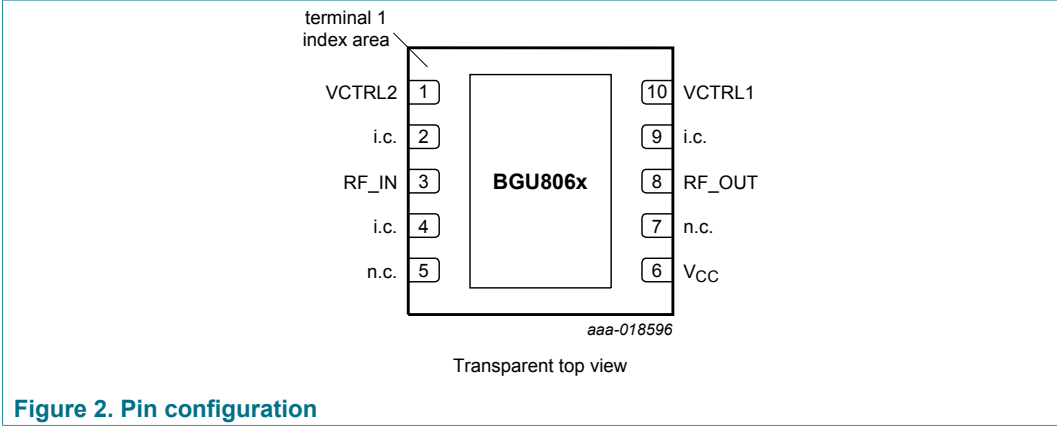


Figure 2. Pin configuration

7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
VCTRL2	1	voltage control 2
i.c.	2, 4, 9	internally connected, can be grounded or left open in the application
RF_IN	3	RF input
n.c.	5	not connected
V _{CC}	6	supply voltage
n.c.	7	not connected
RF_OUT	8	RF output
VCTRL1	10	voltage control 1
GND	exposed die pad	ground

8 Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-	6	V
V _{I(CTRL1)}	input voltage on pin CTRL1		-	3.6	V
V _{I(CTRL2)}	input voltage on pin CTRL2		-	3.6	V
P _{I(RF)CW}	continuous waveform RF input power		-	20	dBm
T _{stg}	storage temperature		-40	+150	°C
T _j	junction temperature		-	150	°C
P	power dissipation	T _{case} ≤ 125 °C [1]	-	510	mW
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM) according to ANSI/ESDA/JEDEC standard JS-001-2010	-	2.0	kV
		Charged Device Model (CDM) according to JEDEC standard 22-C101B	-	1.0	kV

[1] Case is ground solder pad.

9 Recommended operating conditions

Table 5. Table 5. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		4.75	5	5.25	V
Z ₀	characteristic impedance		-	50	-	Ω

10 Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R _{th(j-case)}	thermal resistance from junction to case	[1] [2]	-	55	-	K./W

[1] Case is ground solder pad.

[2] Thermal resistance measured using infrared measurement technique, device mounted on application board and placed in still air.

11 Characteristics

Table 7. Characteristics

$f = 2500$ MHz; $V_{CC} = 5$ V; $T_{amb} = 25$ °C; input and output $50\ \Omega$; unless otherwise specified. All RF parameters are measured on an application board with the circuit as shown in [Figure 29](#) and components listed in [Table 9](#) implemented. This board is optimized for $f = 2500$ MHz.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC}	supply current	LNA enable; bypass off	-	75	90	mA
		LNA disable; bypass on	-	3	5	mA
G_{ass}	associated gain	LNA enable; bypass off	17.0	18.5	20	dB
		LNA disable; bypass on	-2.2	-1.8	-	dB
G_{flat}	gain flatness	within 100 MHz bandwidth; LNA enable; bypass off				
		$2500\text{ MHz} \leq f \leq 4000\text{ MHz}$	-	0.4	-	dB
		$3000\text{ MHz} \leq f \leq 3500\text{ MHz}$	-	0.3	-	dB
NF	noise figure	LNA enable; bypass off ^[1]	-	1.4	2.2	dB
ΔG	gain variation	$2500\text{ MHz} \leq f \leq 4000\text{ MHz}$	-	4.9	-	dB
$P_{L(1dB)}$	output power at 1 dB gain compression	LNA enable; bypass off	17.5	19.0	-	dBm
$IP3_O$	output third-order intercept point	2-tone; tone spacing = 1 MHz; $P_L = 5$ dBm per tone				
		LNA enable; bypass off	31.0	34.0	-	dBm
		LNA disable; bypass on	-	43.0	-	dBm
RL_{in}	input return loss	LNA enable; bypass off	-	-10	-	dB
		LNA disable; bypass on	-	-20	-	dB
RL_{out}	output return loss	LNA enable; bypass off	-	-10	-	dB
		LNA disable; bypass on	-	-20	-	dB
ISL	isolation	LNA disable; bypass off	-	30	-	dB
		LNA enable; bypass off	-	25	-	dB
$t_{s(pon)}$	power-on settling time	$P_i = -20$ dBm	-	0.5	-	μ s
$t_{s(poff)}$	power-off settling time	$P_i = -20$ dBm	-	0.1	-	μ s
K	Rollett stability factor	both on-state and off-state up to $f = 20$ GHz	1	-	-	-

[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

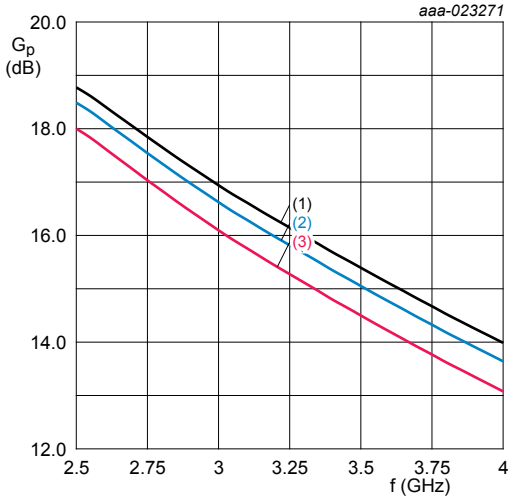
Table 8. Control truth table

 $V_{CC} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Control signal setting ^[1]		Mode of operation	
CTRL1	CTRL2	LNA	bypass
LOW	HIGH	disable	on
HIGH	HIGH	disable	on
LOW	LOW	enable	off
HIGH	LOW	disable	off

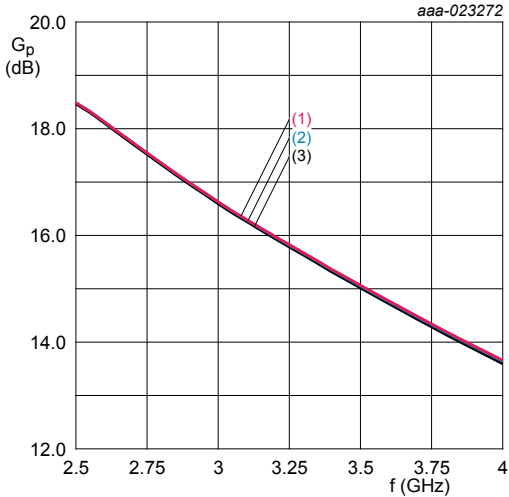
- [1] A logic LOW is the result of an input voltage on that specific pin between -0.3 V and $+0.7\text{ V}$.
A logic HIGH is the result of an input voltage on that specific pin between 1.2 V and 3.6 V .

12 Graphics



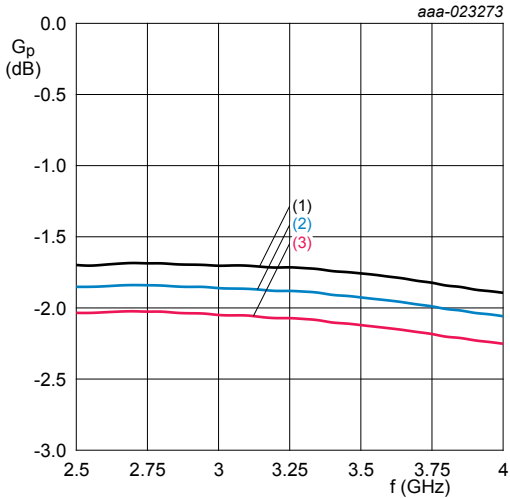
$V_{CC} = 5\text{ V}$
(1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
(2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = +95\text{ }^{\circ}\text{C}$

Figure 3. Power gain as a function of frequency - Gain mode; typical values



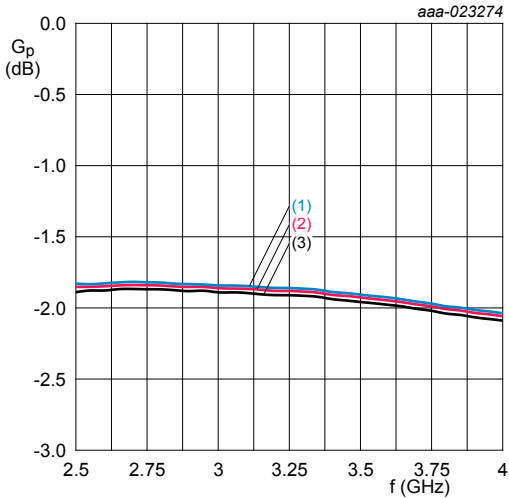
$T_{amb} = +25\text{ }^{\circ}\text{C}$
(1) $V_{CC} = 4.75\text{ V}$
(2) $V_{CC} = 5\text{ V}$
(3) $V_{CC} = 5.25\text{ V}$

Figure 4. Power gain as a function of frequency - Gain mode; typical values



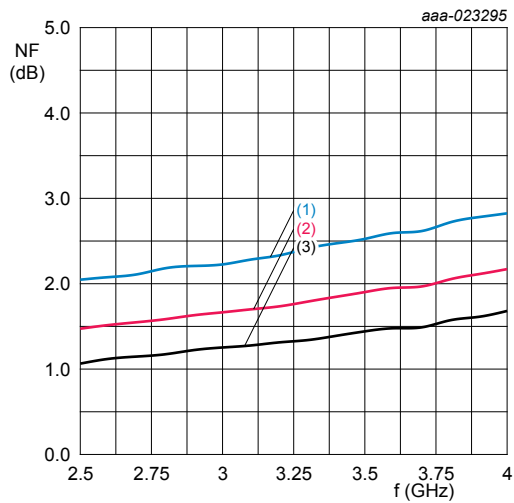
$V_{CC} = 5\text{ V}$
(1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
(2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = +95\text{ }^{\circ}\text{C}$

Figure 5. Power gain as a function of frequency - Bypass mode; typical values



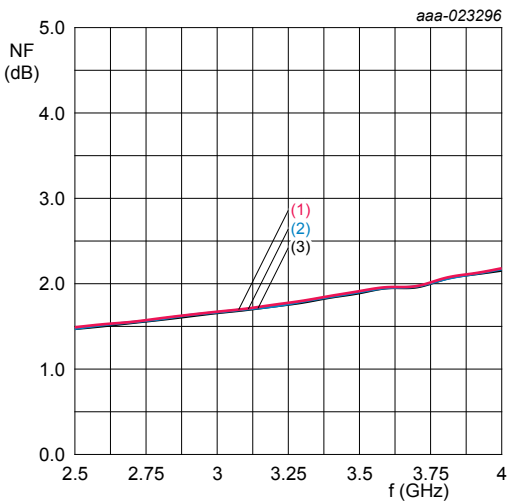
$T_{amb} = +25\text{ }^{\circ}\text{C}$
(1) $V_{CC} = 4.75\text{ V}$
(2) $V_{CC} = 5\text{ V}$
(3) $V_{CC} = 5.25\text{ V}$

Figure 6. Power gain as a function of frequency - Bypass mode; typical values



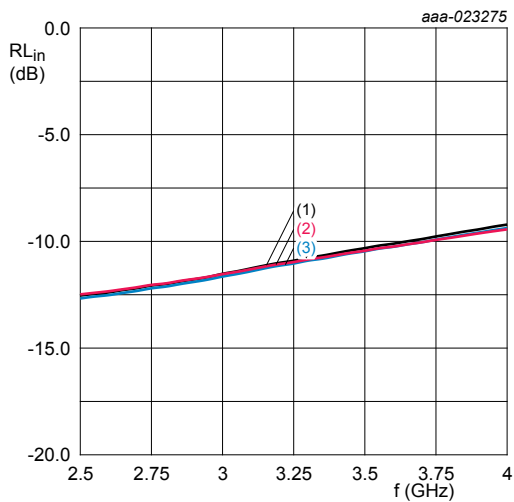
$V_{CC} = 5\text{ V}$
(1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
(2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = +95\text{ }^{\circ}\text{C}$

Figure 7. Noise figure as a function of frequency - Gain mode; typical values



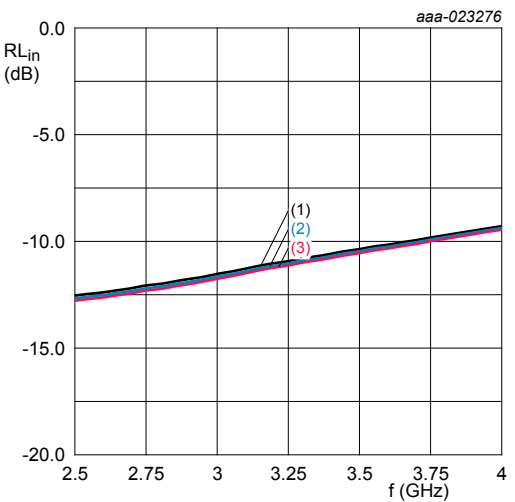
$T_{amb} = +25\text{ }^{\circ}\text{C}$
(1) $V_{CC} = 4.75\text{ V}$
(2) $V_{CC} = 5\text{ V}$
(3) $V_{CC} = 5.25\text{ V}$

Figure 8. Noise figure as a function of frequency - Gain mode; typical values



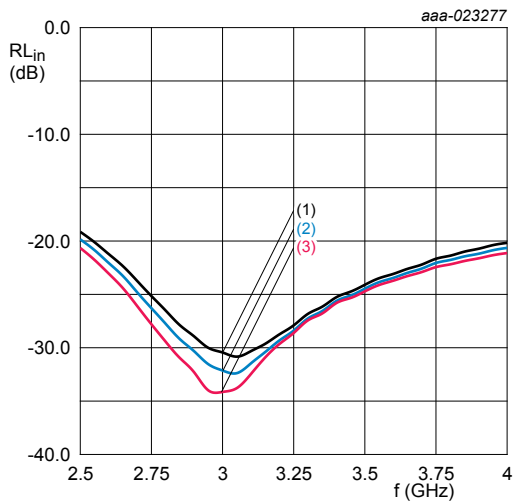
$V_{CC} = 5\text{ V}$
(1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
(2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = +95\text{ }^{\circ}\text{C}$

Figure 9. Input return loss as a function of frequency - Gain mode; typical values



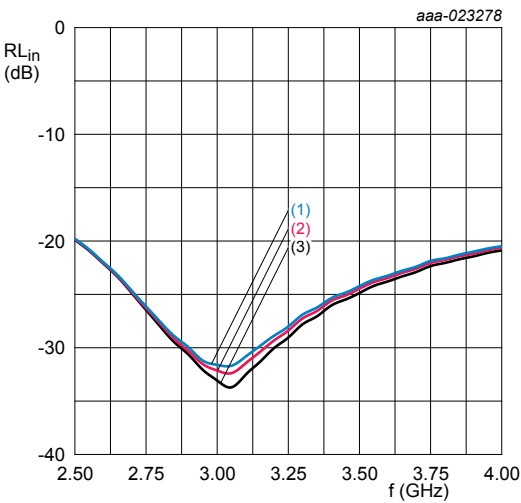
$T_{amb} = +25\text{ }^{\circ}\text{C}$
(1) $V_{CC} = 4.75\text{ V}$
(2) $V_{CC} = 5\text{ V}$
(3) $V_{CC} = 5.25\text{ V}$

Figure 10. Input return loss as a function of frequency - Gain mode; typical values



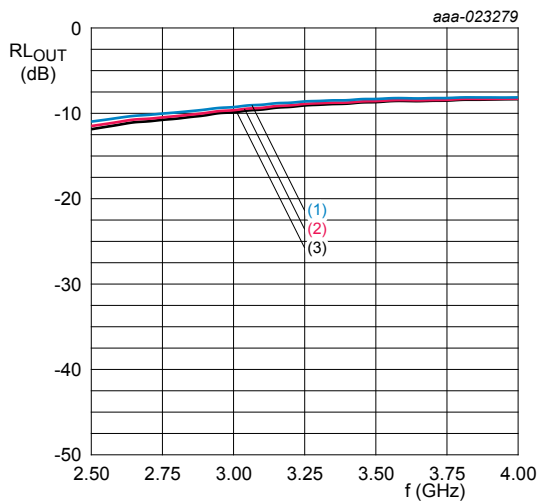
V_{CC} = 5 V
(1) T_{amb} = -40 °C
(2) T_{amb} = +25 °C
(3) T_{amb} = +95 °C

Figure 11. Input return loss as a function of frequency - Bypass mode; typical values



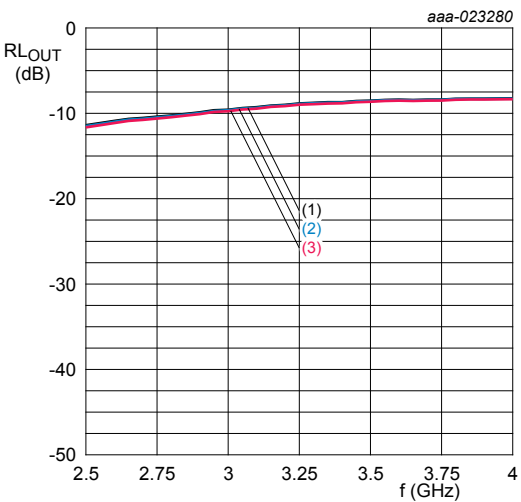
T_{amb} = +25 °C
(1) V_{CC} = 4.75 V
(2) V_{CC} = 5 V
(3) V_{CC} = 5.25 V

Figure 12. Input return loss as a function of frequency - Bypass mode; typical values



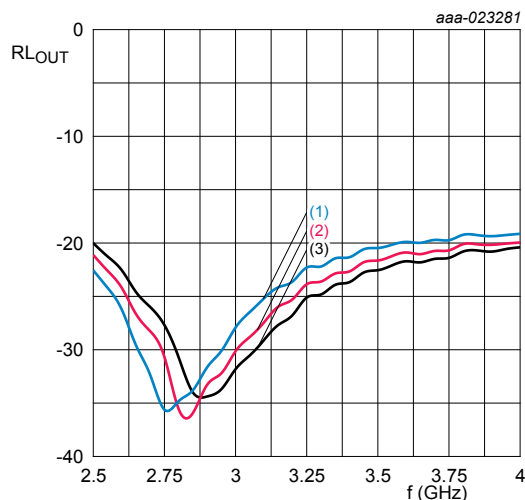
V_{CC} = 5 V
(1) T_{amb} = -40 °C
(2) T_{amb} = +25 °C
(3) T_{amb} = +95 °C

Figure 13. Output return loss as a function of frequency- Gain mode; typical values



T_{amb} = +25 °C
(1) V_{CC} = 4.75 V
(2) V_{CC} = 5 V
(3) V_{CC} = 5.25 V

Figure 14. Output return loss as a function of frequency- Gain mode; typical values



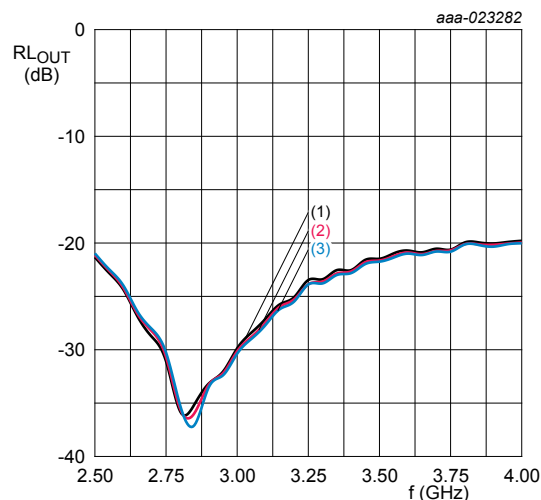
$V_{CC} = 5 \text{ V}$

(1) $T_{amb} = -40 \text{ }^{\circ}\text{C}$

(2) $T_{amb} = +25 \text{ }^{\circ}\text{C}$

(3) $T_{amb} = +95 \text{ }^{\circ}\text{C}$

Figure 15. Output return loss as a function of frequency - Bypass mode; typical values



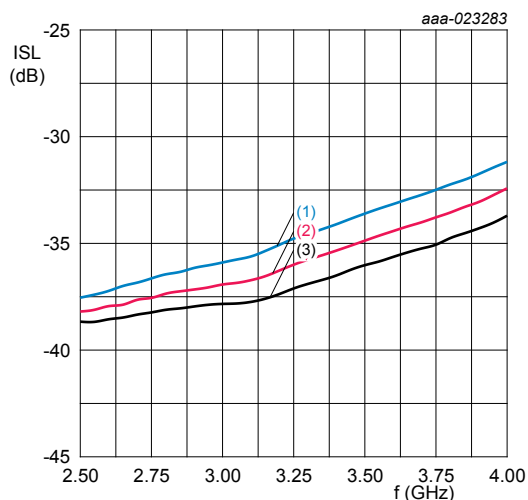
$T_{amb} = +25 \text{ }^{\circ}\text{C}$

(1) $V_{CC} = 4.75 \text{ V}$

(2) $V_{CC} = 5 \text{ V}$

(3) $V_{CC} = 5.25 \text{ V}$

Figure 16. Output return loss as a function of frequency - Bypass mode; typical values



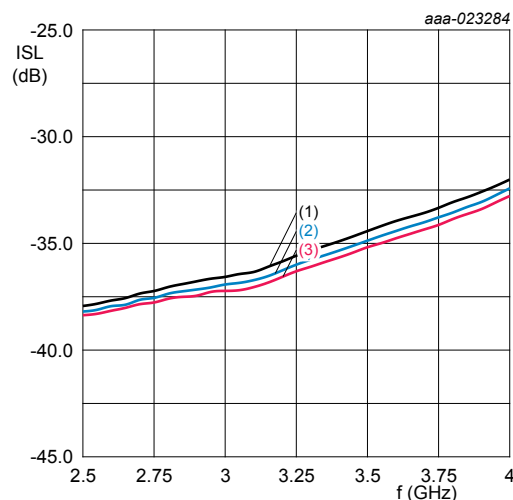
$V_{CC} = 5 \text{ V}$

(1) $T_{amb} = -40 \text{ }^{\circ}\text{C}$

(2) $T_{amb} = +25 \text{ }^{\circ}\text{C}$

(3) $T_{amb} = +95 \text{ }^{\circ}\text{C}$

Figure 17. Isolation as a function of frequency - isolation mode; typical values



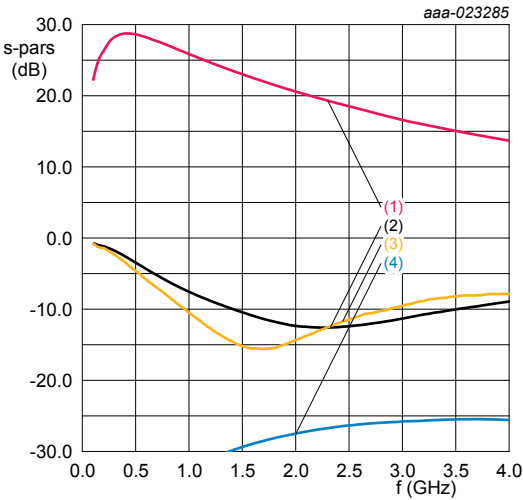
$T_{amb} = +25 \text{ }^{\circ}\text{C}$

(1) $V_{CC} = 4.75 \text{ V}$

(2) $V_{CC} = 5 \text{ V}$

(3) $V_{CC} = 5.25 \text{ V}$

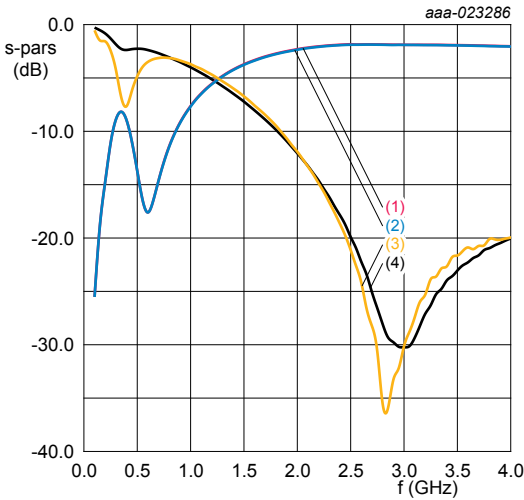
Figure 18. Isolation as a function of frequency - Isolation mode; typical values



$V_{CC} = 5\text{ V}$; $T_{amb} = +25\text{ }^{\circ}\text{C}$

- (1) S11
- (2) S21
- (3) S12
- (4) S22

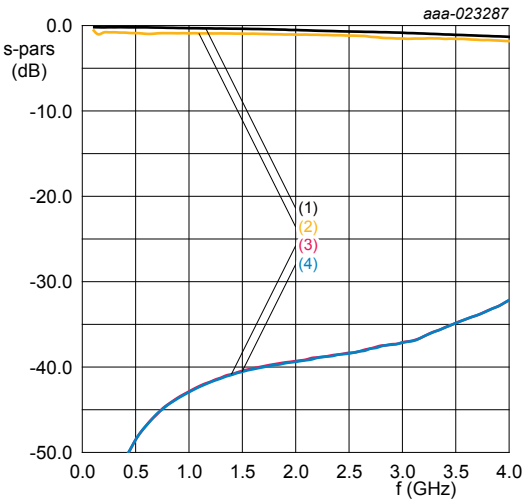
Figure 19. Wideband S-parameters as function of frequency - Gain mode; typical values



$V_{CC} = 5\text{ V}$; $T_{amb} = +25\text{ }^{\circ}\text{C}$

- (1) S11
- (2) S21
- (3) S12
- (4) S22

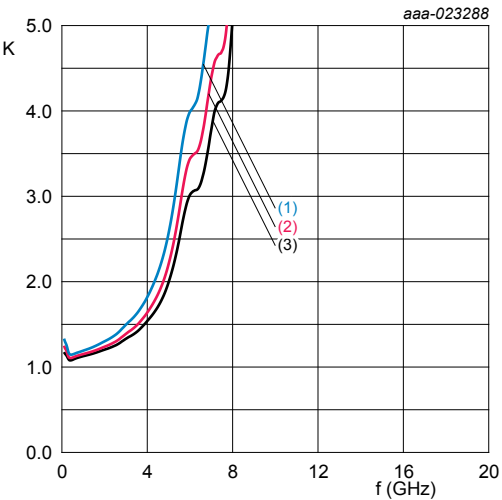
Figure 20. Wideband S-parameters as function of frequency - Bypass mode; typical values



$V_{CC} = 5\text{ V}$; $T_{amb} = +25\text{ }^{\circ}\text{C}$

- (1) S11
- (2) S21
- (3) S12
- (4) S22

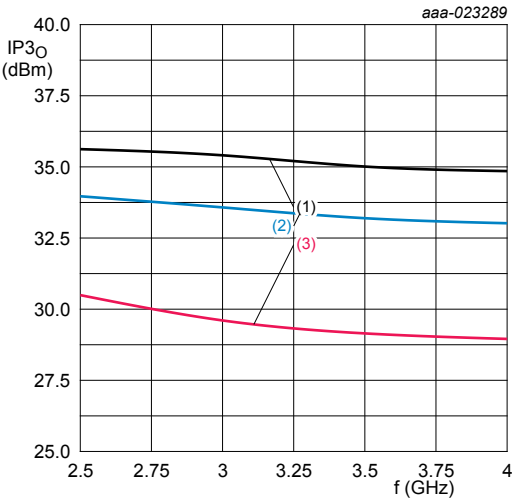
Figure 21. Wideband S-parameters as function of frequency - Isolation mode; typical values



$V_{CC} = 5\text{ V}$

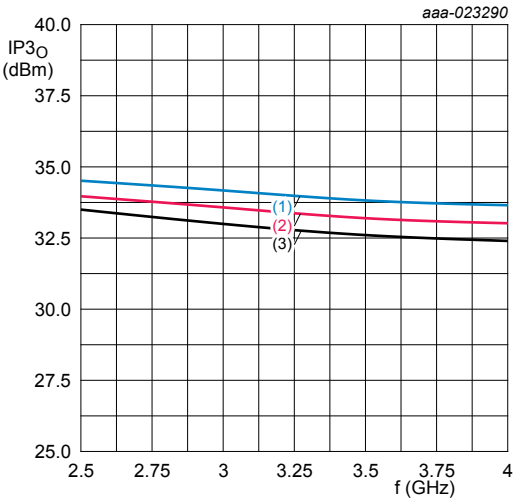
- (1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = +95\text{ }^{\circ}\text{C}$

Figure 22. Rollett Stability factor as function of frequency - Gain mode; typical values



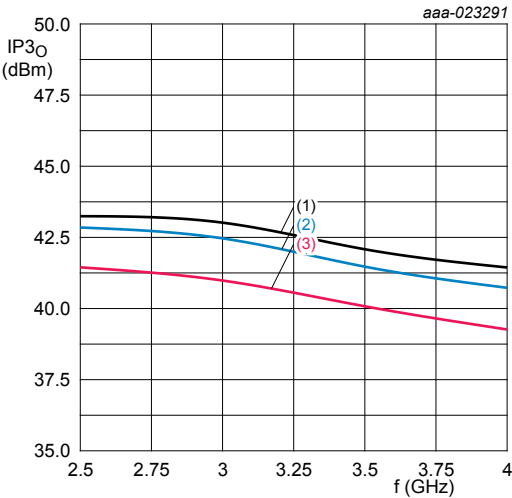
$V_{CC} = 5\text{ V}$
(1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
(2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = +95\text{ }^{\circ}\text{C}$

Figure 23. Output third-order intercept point as a function of frequency - Gain mode; typical values



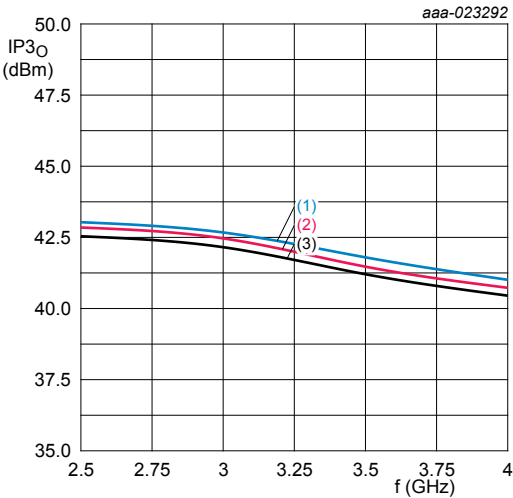
$T_{amb} = +25\text{ }^{\circ}\text{C}$
(1) $V_{CC} = 4.75\text{ V}$
(2) $V_{CC} = 5\text{ V}$
(3) $V_{CC} = 5.25\text{ V}$

Figure 24. Output third-order intercept point as a function of frequency - Gain mode; typical values



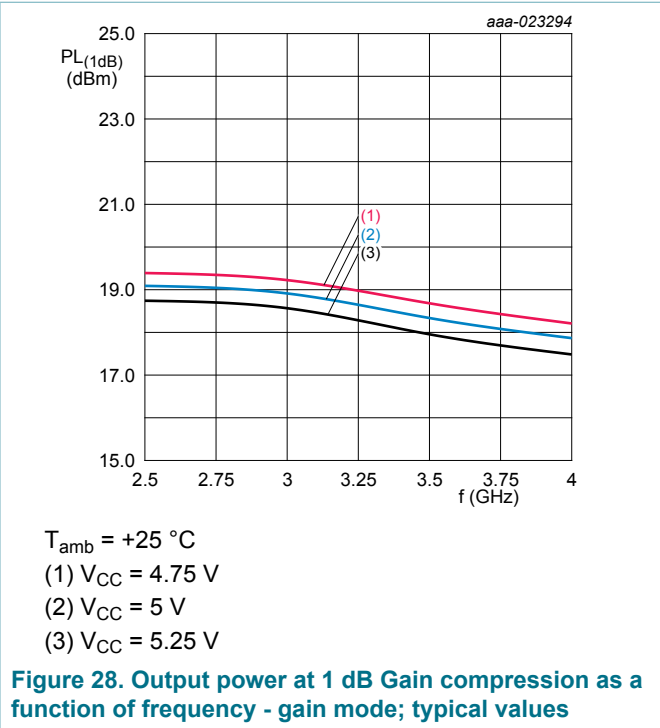
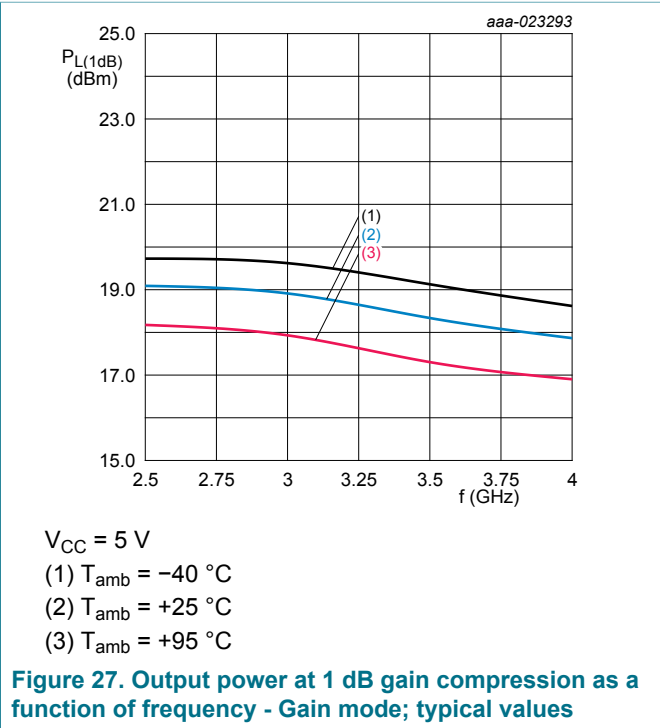
$V_{CC} = 5\text{ V}$
(1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
(2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = +95\text{ }^{\circ}\text{C}$

Figure 25. Output third-order intercept point as a function of frequency - Bypass mode; typical values



$T_{amb} = +25\text{ }^{\circ}\text{C}$
(1) $V_{CC} = 4.75\text{ V}$
(2) $V_{CC} = 5\text{ V}$
(3) $V_{CC} = 5.25\text{ V}$

Figure 26. Output third-order intercept point as a function of frequency - Bypass mode; typical values



13 Application information

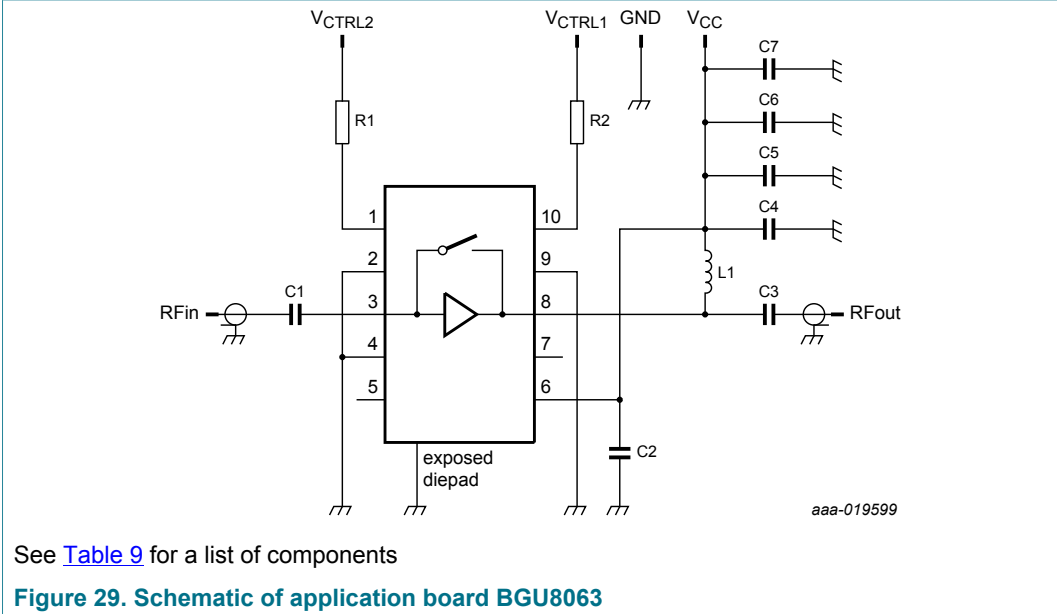


Table 9. List of components

See [Figure 29](#) for schematics.

Component	Description	Value	Remarks
C1	capacitor	100 nF	
C2, C3	capacitor	100 pF	
C4	capacitor	1 nF	
C5	capacitor	-	optional
C6	capacitor	10 nF	
C7	capacitor	1 µF	
L1	inductor	15 nH	
R1, R2	resistor	1 kΩ	

14 Package outline

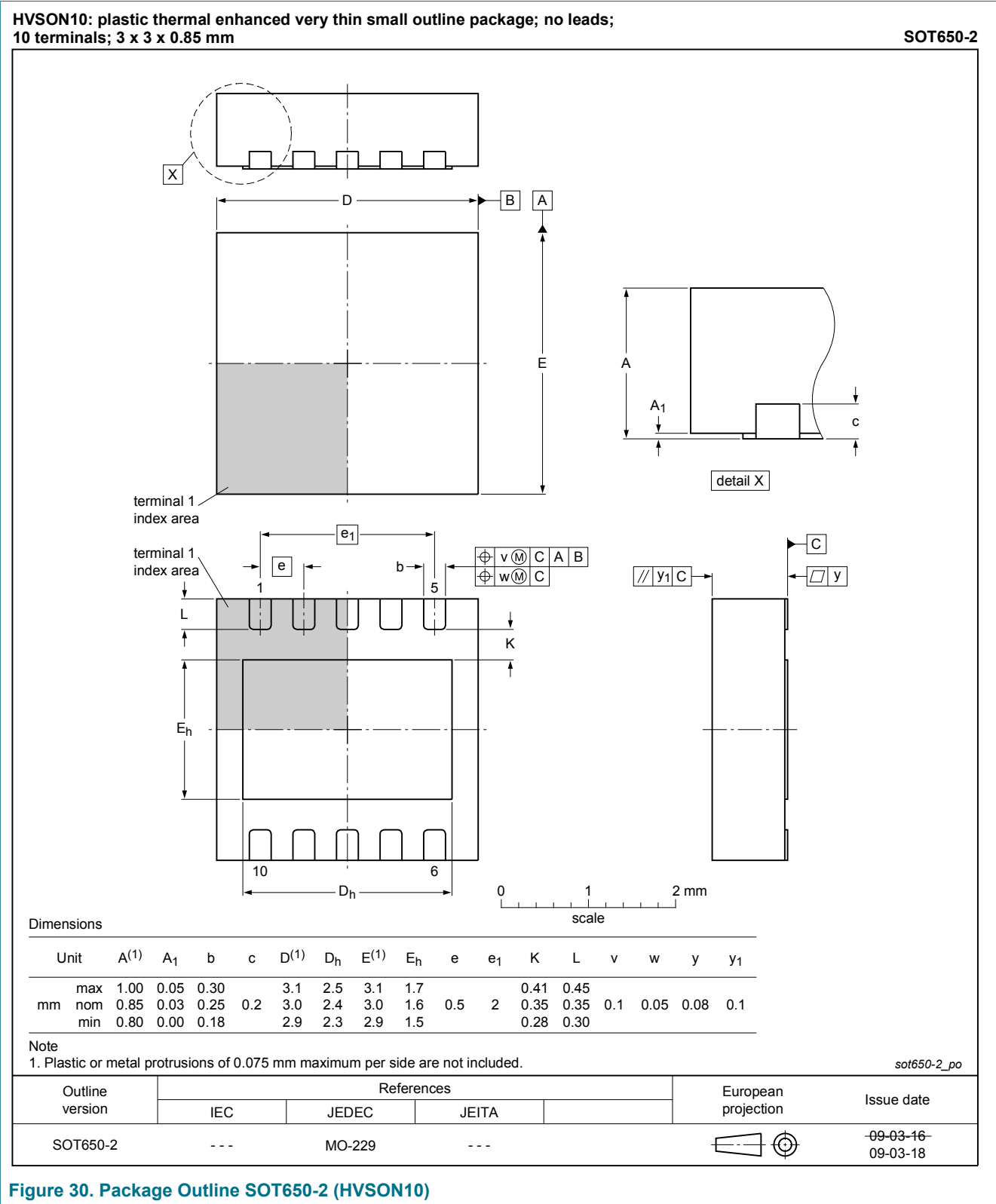


Figure 30. Package Outline SOT650-2 (HVSON10)

15 Abbreviations

Table 10. Abbreviations

Acronym	Description
CDMA	Code Division Multiple Access
ESD	ElectroStatic Discharge
FDD	Frequency-Division Duplexing
GSM	Global System for Mobile communication
LNA	Low Noise Amplifier
LTE	Long Term Evolution
TDD	Time-Division Duplexing
W-CDMA	Wideband Code Division Multiple Access

16 Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU8063 v.2	20170127	product data sheet	-	BGU8063 v.1
Modifications:	• Section 1 : added BTS3001H according to our new naming convention			
BGU8063 v.1	20170118	product data sheet	-	-

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Document identifier: BGU8063



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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